

Spiral Band Structure Hidden in the Bulk Chiral Crystal NbSi₂

Cheng Zhang^a, Koji Miyamoto^a, Tatsuya Shishidou^b, Ryoga Amano^c, Taisei Sayo^c, Chiho Shimada^c, Yusuke Kousaka^c, Michael Weinert^b, Yoshihiko Togawa^c, and Taichi Okuda^a

^aHiroshima synchrotron Radiation Center, Hiroshima University, Higashi-Hiroshima 739-0046, Japan.

^b Department of Physics, University of Wisconsin-Milwaukee, Wisconsin 53201, USA.

^c Department of Physics and Electronics, Osaka Metropolitan University, Osaka 599-8531, Japan.

Keywords: Chiral crystal, Spiral band structure, ARPES, DFT.

Recently, so-called chirality induced spin selectivity effect (CISS) has been observed in the chiral crystal NbSi₂ through electrical conductivity measurement [1], CISS effect refers to a phenomenon that a spin-polarized current is generated when a current is passed through a material with a chiral structure [2,3].

To investigate the electronic structure of NbSi₂, we performed synchrotron-radiation angle resolved photoemission spectroscopy for both right-(P₆₂₂) and left-handed (P₆₄₂₂) samples. Since the NbSi₂ crystal is difficult to cleave, the clean surface was obtained by mechanical polishing, Ar ion sputtering and annealing. We found not only the clear energy bands, but also spiral-shaped constant energy contours (CEC) at specific binding energies (E_B). The fact that the helicity of this pattern is reversed in the crystal having opposite chirality indicates that the observed intriguing pattern has its origin in the structural chirality. Our density functional theory (DFT) calculations confirmed this point. This result demonstrates that a photoemission experiment can be a new way to distinguish the chirality of crystals.

Figure 1 (a) and (b) show energy band structure of the right-handed NbSi₂ observed by ARPES along the high-symmetry lines $\bar{M}-\bar{\Gamma}-\bar{M}$ and $\bar{K}-\bar{\Gamma}-\bar{K}$. Figure 1 (c) and (d) show the bulk and surface calculated energy band structure, respectively. Bulk bands and surface states of ARPES data can be distinguished. Figure 2 (a) and (b) are CEC patterns for the right- and left-handed NbSi₂, respectively. Figure 2 (c) and (d) are the bulk calculated results without the showing spiral patterns. By comparing the surface calculated results, as shown in Figure 2 (e) and (f), we can confirm that the spiral structure is a surface effect.

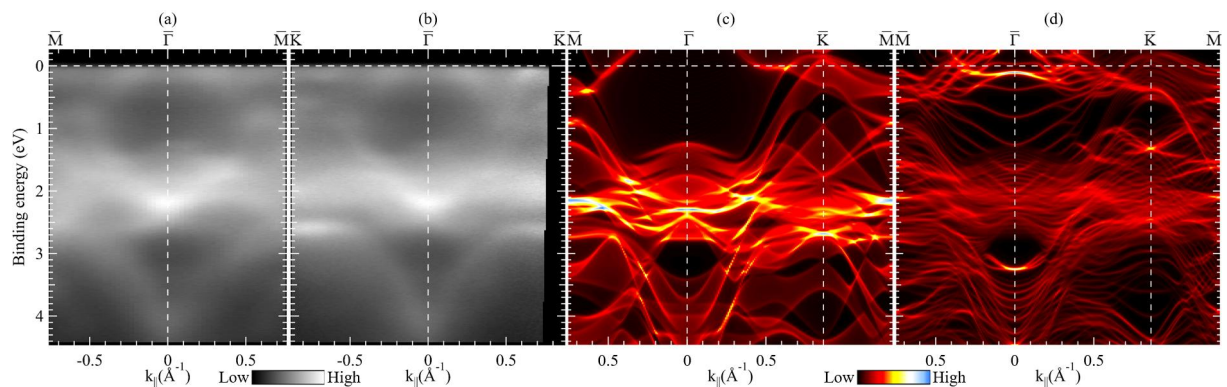


Figure 1. (a), (b) ARPES band structures of right-handed NbSi₂ crystal (P6₂22) along lines $\bar{M}-\bar{\Gamma}-\bar{M}$ and $\bar{K}-\bar{\Gamma}-\bar{K}$. (c), (d) Bulk and surface calculated energy band structures by DFT along the high-symmetry lines.

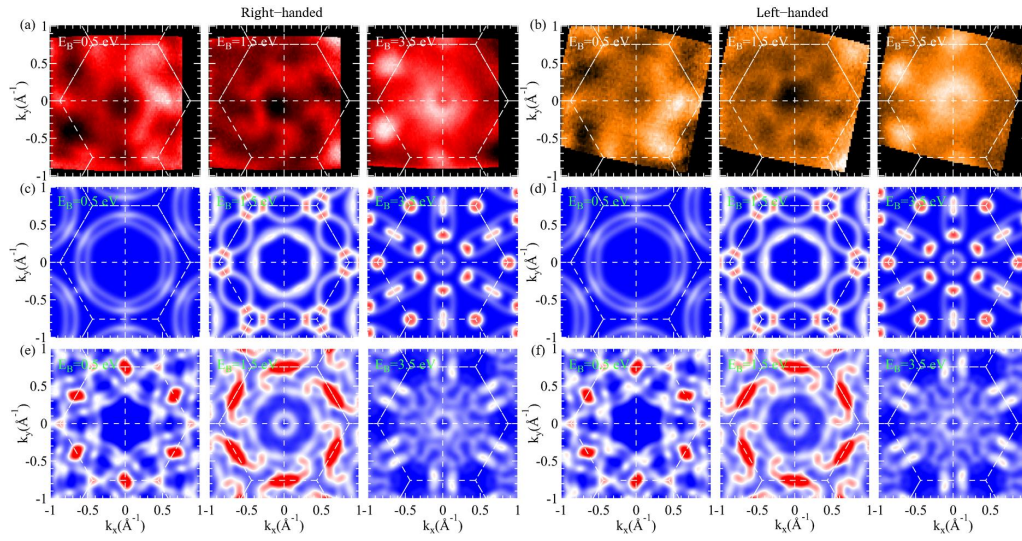


Figure 2. (a), (b) ARPES CEC patterns for the right-handed (P6₂22) and left-handed NbSi₂ (P6₄22) at some typical E_B , respectively, which are constant energy cut at E_B through a $E(k_x, k_y)$ data set obtained at a photon energy of 50 eV. (c), (d) Bulk calculated results for some corresponding E_B . (e), (f) Surface calculated results.

REFERENCES

- [1] Kohei Shiota, Akito Inui et al., Chirality-Induced Spin Polarization over Macroscopic Distances in Chiral Disilicide Crystals, Phys. Rev. Lett. ,127, 126602 (2021).
- [2] R. Naaman and D. H. Waldeck, Chiral-induced spin selectivity effect, J. Phys. Chem. Lett. 3, 2178 (2012).
- [3] R. Naaman and D. H. Waldeck, Spintronics and chirality: Spin selectivity in electron transport through chiral molecules, Annu. Rev. Phys. Chem. 66, 263 (2015).